

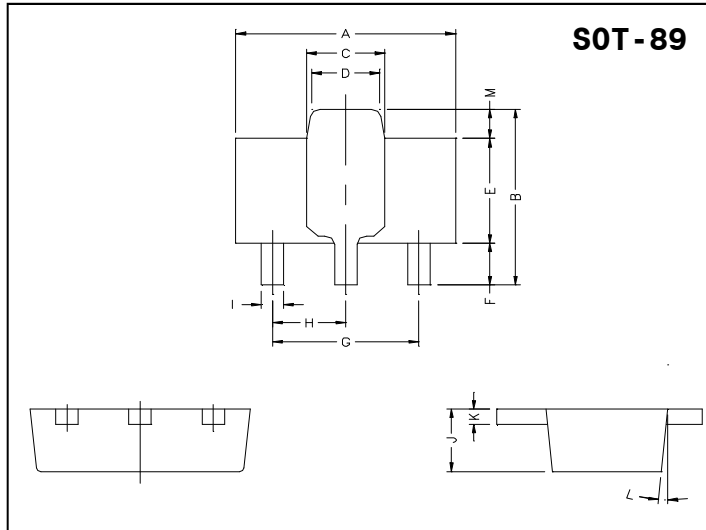
## GM8550

PNP EPITAXIAL TRANSISTOR

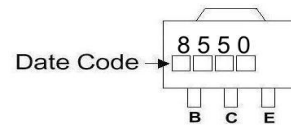
### Description

The GM8550 is designed for use in 1W output amplifier of portable radios in class B push-pull operation.

### Package Dimensions



### Marking :



| Millimeter |      |      | Millimeter |      |      |
|------------|------|------|------------|------|------|
|            | Min. | Max. |            | Min. | Max. |
| A          | 4.4  | 4.6  | G          | 3.00 | REF. |
| B          | 4.05 | 4.25 | H          | 1.50 | REF. |
| C          | 1.50 | 1.70 | I          | 0.40 | 0.52 |
| D          | 1.30 | 1.50 | J          | 1.40 | 1.60 |
| E          | 2.40 | 2.60 | K          | 0.35 | 0.41 |
| F          | 0.89 | 1.20 | L          | 5°   | TYP. |
|            |      |      | M          | 0.70 | REF. |

### Absolute Maximum Ratings at Ta = 25°C

| Parameter                    | Symbol           | Ratings    | Unit |
|------------------------------|------------------|------------|------|
| Junction Temperature         | T <sub>j</sub>   | +150       | °C   |
| Storage Temperature          | T <sub>stg</sub> | -55 ~ +150 | °C   |
| Collector to Base Voltage    | BVCBO            | -40        | V    |
| Collector to Emitter Voltage | BVCEO            | -25        | V    |
| Emitter to Base Voltage      | BVEBO            | -6         | V    |
| Collector Current            | I <sub>C</sub>   | -1.5       | A    |
| Base Current                 | I <sub>B</sub>   | -0.5       | A    |
| Total Power Dissipation      | PD               | 1          | W    |

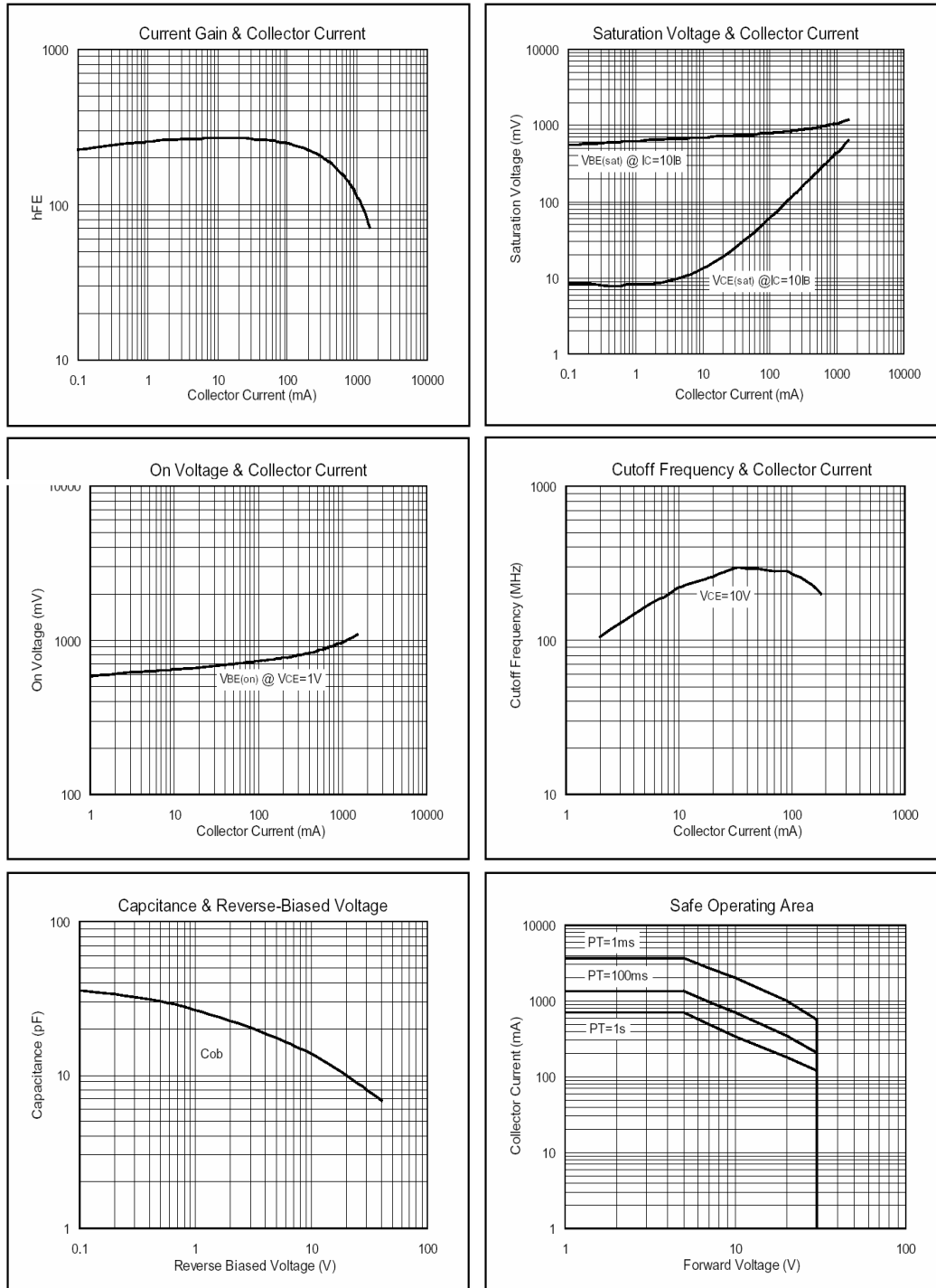
### Characteristics at Ta = 25°C

| Symbol         | Min. | Typ. | Max. | Unit | Test Conditions                                        |
|----------------|------|------|------|------|--------------------------------------------------------|
| BVCBO          | -40  | -    | -    | V    | I <sub>C</sub> =-100uA                                 |
| BVCEO          | -25  | -    | -    | V    | I <sub>C</sub> =-2mA                                   |
| BVEBO          | -6   | -    | -    | V    | I <sub>E</sub> =-100uA                                 |
| ICBO           | -    | -    | -100 | nA   | V <sub>CB</sub> =-35V                                  |
| IEBO           | -    | -    | -100 | nA   | V <sub>EB</sub> =-6V                                   |
| VCE(sat)       | -    | -    | -0.5 | V    | I <sub>C</sub> =-0.8A, I <sub>B</sub> =-80mA           |
| VBE(sat)       | -    | -    | -1.2 | V    | I <sub>C</sub> =-0.8A, I <sub>B</sub> =-80mA           |
| VBE(on)        | -    | -    | -1   | V    | V <sub>CE</sub> =-1V, I <sub>C</sub> =-10mA            |
| hfe1           | 45   | -    | -    |      | V <sub>CE</sub> =-1V, I <sub>C</sub> =-5mA             |
| hfe2           | 120  | -    | 500  |      | V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA           |
| hfe3           | 40   | -    | -    |      | V <sub>CE</sub> =-1V, I <sub>C</sub> =-800mA           |
| f <sub>T</sub> | 100  | -    | -    | MHz  | V <sub>CE</sub> =-10V, I <sub>C</sub> =-20mA, f=100MHz |

### Classification Of hFE

| Rank | C         | D         | E         |
|------|-----------|-----------|-----------|
| hFE  | 120 - 200 | 160 - 300 | 250 - 500 |

## Characteristics Curve



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